

MBR150, MBR160

MBR160 is a Preferred Device

Axial Lead Rectifiers

The MBR150/160 series employs the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlap contact. Ideally suited for use as rectifiers in low-voltage, high-frequency inverters, free wheeling diodes, and polarity protection diodes.

Features

- Low Reverse Current
- Low Stored Charge, Majority Carrier Conduction
- Low Power Loss/High Efficiency
- Highly Stable Oxide Passivated Junction
- These devices are manufactured with a Pb-Free external lead finish only*

Mechanical Characteristics

- Case: Epoxy, Molded
- Weight: 0.4 gram (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 220°C Max. for 10 Seconds, 1/16" from case
- Shipped in Plastic Bags, 1000 per bag
- Available Tape and Reeled, 5000 per reel, by adding a "RL" suffix to the part number
- Polarity: Cathode Indicated by Polarity Band

勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-54151736
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ON Semiconductor®

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SCHOTTKY BARRIER RECTIFIERS

1.0 AMPERE

50, 60 VOLTS



MARKING DIAGRAM



MBR1x0 = Device Code
x = 5 or 6

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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MAXIMUM RATINGS

Rating	Symbol	MBR150	MBR160	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	60	V
RMS Reverse Voltage	$V_{R(RMS)}$	35	42	V
Average Rectified Forward Current (Note 1) ($V_{R(equiv)} \leq 0.2 V_R(dc)$, $T_L = 90^\circ C$, $R_{\theta JA} = 80^\circ C/W$, P.C. Board Mounting, $T_A = 55^\circ C$)	I_O	1.0		A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions, halfwave, single phase, 60 Hz, $T_L = 70^\circ C$)	I_{FSM}	25 (for one cycle)		A
Operating and Storage Junction Temperature Range (Reverse Voltage Applied)	T_J, T_{stg}	- 65 to +150		$^\circ C$
Peak Operating Junction Temperature (Forward Current Applied)	$T_{J(pk)}$	150		$^\circ C$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS (Notes 1 and 2)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	80	$^\circ C/W$

ELECTRICAL CHARACTERISTICS ($T_L = 25^\circ C$ unless otherwise noted) (Note 1)

Characteristic	Symbol	Max	Unit
Maximum Instantaneous Forward Voltage (Note 2) ($i_F = 0.1 A$) ($i_F = 1.0 A$) ($i_F = 3.0 A$)	V_F	0.550 0.750 1.000	V
Maximum Instantaneous Reverse Current @ Rated dc Voltage (Note 2) ($T_L = 25^\circ C$) ($T_L = 100^\circ C$)	i_R	0.5 5.0	mA

- Lead Temperature reference is cathode lead 1/32" from case.
- Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

ORDERING INFORMATION

Device	Package	Shipping†
MBR150	Axial Lead (Pb-Free)	1000 Units / Bag
MBR150RL	Axial Lead (Pb-Free)	5000 / Tape & Reel
MBR160	Axial Lead (Pb-Free)	1000 Units / Bag
MBR160RL	Axial Lead (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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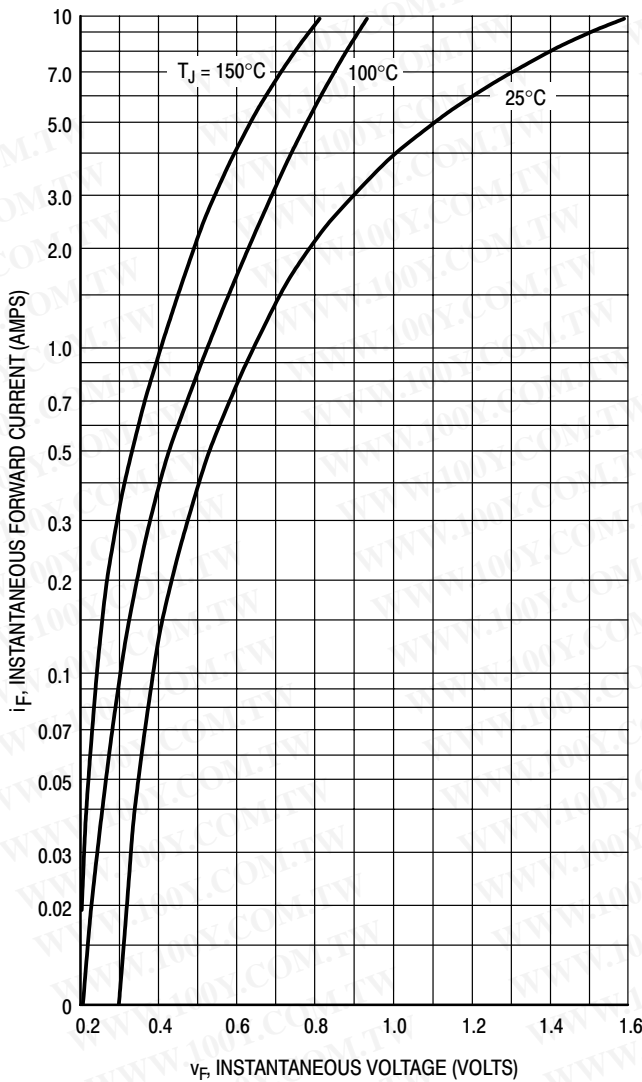


Figure 1. Typical Forward Voltage

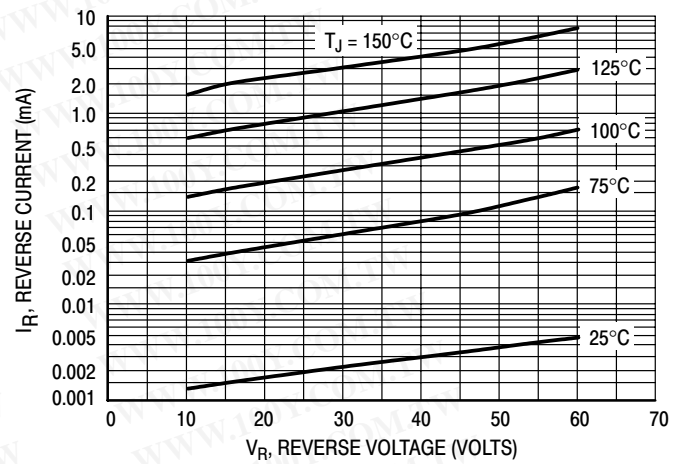


Figure 2. Typical Reverse Current*

*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_R is sufficiently below rated V_R .

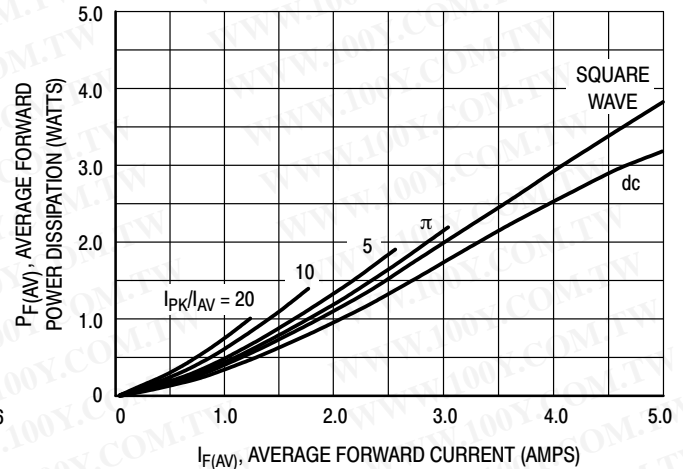


Figure 3. Forward Power Dissipation

THERMAL CHARACTERISTICS

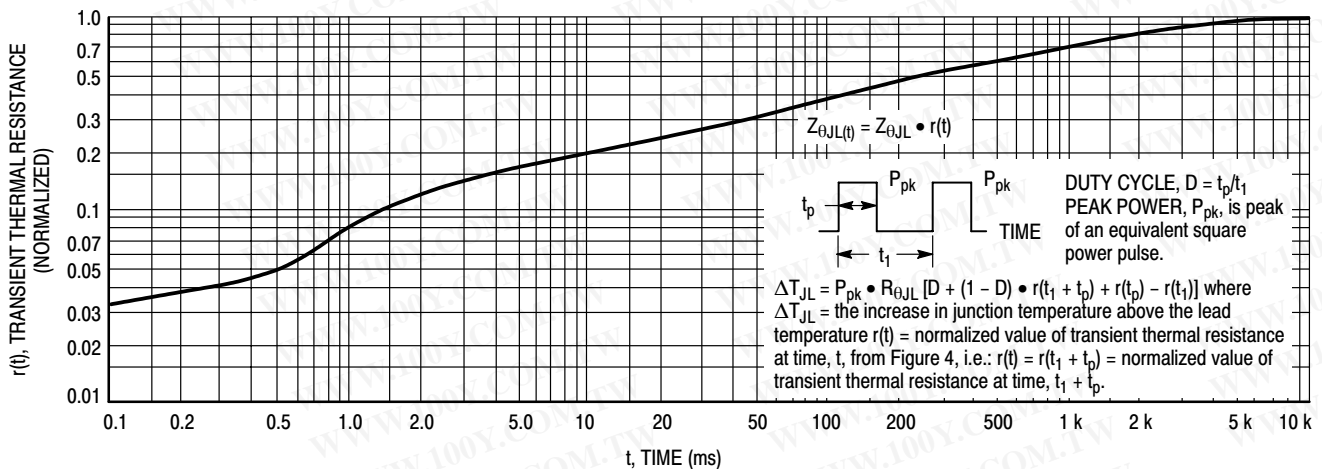


Figure 4. Thermal Response

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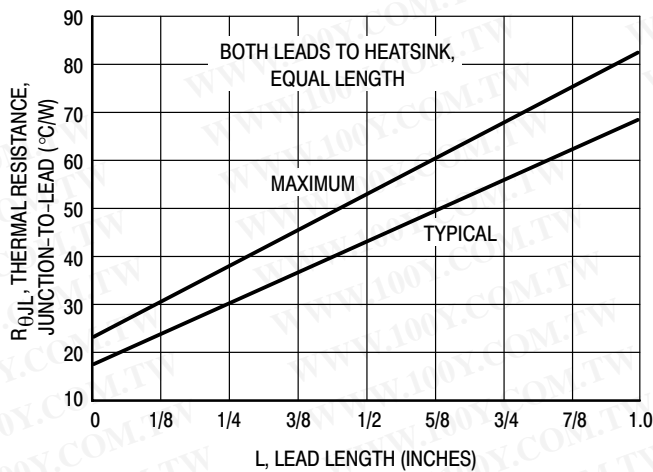


Figure 5. Steady-State Thermal Resistance

NOTE 1. — MOUNTING DATA:

Data shown for thermal resistance junction-to-ambient ($R_{\theta JA}$) for the mounting shown is to be used as a typical guideline values for preliminary engineering or in case the tie point temperature cannot be measured.

Typical Values for $R_{\theta JA}$ in Still Air

Mounting Method	Lead Length, L (in)				$R_{\theta JA}$
	1/8	1/4	1/2	3/4	
1	52	65	72	85	°C/W
2	67	80	87	100	°C/W
3	—	—	50	—	°C/W

NOTE 2. — THERMAL CIRCUIT MODEL:

(For heat conduction through the leads)

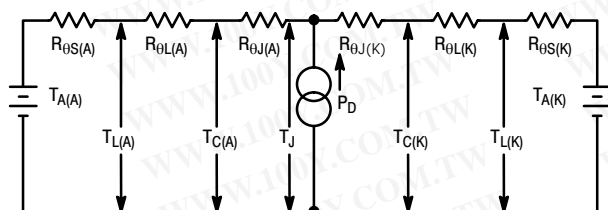
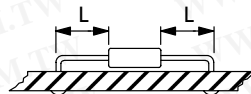


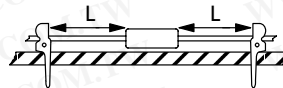
Figure 6. Typical Capacitance

Mounting Method 1

P.C. Board with
1-1/2" x 1-1/2"
copper surface.



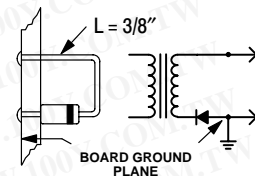
Mounting Method 2



VECTOR PIN MOUNTING

Mounting Method 3

P.C. Board with
1-1/2" x 1-1/2"
copper surface.



(Subscripts A and K refer to anode and cathode sides, respectively.) Values for thermal resistance components are: $R_{\theta L} = 100^\circ\text{C/W/in}$ typically and 120°C/W/in maximum. $R_{\theta J} = 36^\circ\text{C/W}$ typically and 46°C/W maximum.

NOTE 3. — HIGH FREQUENCY OPERATION:

Since current flow in a Schottky rectifier is the result of majority carrier conduction, it is not subject to junction diode forward and reverse recovery transients due to minority carrier injection and stored charge. Satisfactory circuit analysis work may be performed by using a model consisting of an ideal diode in parallel with a variable capacitance. (See Figure 6)

Rectification efficiency measurements show that operation will be satisfactory up to several megahertz. For example, relative waveform rectification efficiency is approximately 70 percent at 2 MHz, e.g., the ratio of dc power to RMS power in the load is 0.28 at this frequency, whereas perfect rectification would yield 0.406 for sine wave inputs. However, in contrast to ordinary junction diodes, the loss in waveform efficiency is not indicative of power loss: it is simply a result of reverse current flow through the diode capacitance, which lowers the dc output voltage.

Use of the above model permits junction to lead thermal resistance for any mounting configuration to be found. For a given total lead length, lowest values occur when one side of the rectifier is brought as close as possible to the heatsink. Terms in the model signify:

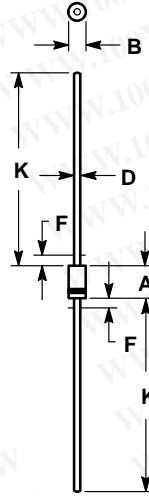
T_A = Ambient Temperature T_C = Case Temperature
 T_L = Lead Temperature T_J = Junction Temperature
 $R_{\theta S}$ = Thermal Resistance, Heatsink-to-Ambient
 $R_{\theta L}$ = Thermal Resistance, Lead-to-Heatsink
 $R_{\theta J}$ = Thermal Resistance, Junction-to-Case
 P_D = Power Dissipation

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PACKAGE DIMENSIONS

AXIAL LEAD, DO-41 CASE 59-10 ISSUE S



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 59-04 OBSOLETE, NEW STANDARD 59-09.
4. 59-03 OBSOLETE, NEW STANDARD 59-10.
5. ALL RULES AND NOTES ASSOCIATED WITH JEDEC DO-41 OUTLINE SHALL APPLY
6. POLARITY DENOTED BY CATHODE BAND.
7. LEAD DIAMETER NOT CONTROLLED WITHIN F DIMENSION.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.161	0.205	4.10	5.20
B	0.079	0.106	2.00	2.70
D	0.028	0.034	0.71	0.86
F	---	0.050	---	1.27
K	1.000	---	25.40	---

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